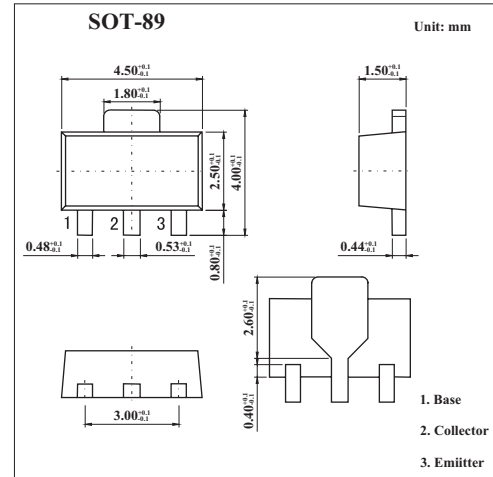


Surface Mount PNP Silicon Transistor

KXT5401 (CXT5401)

■ Features

- High current (max. 500mA).
- Low voltage (max. 150 V).



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-160	V
Collector-emitter voltage	V_{CE0}	-150	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current (DC)	I_c	-500	mA
power dissipation	P_D	1.2	W
thermal resistance Junction- to-ambient	$R_{\theta JA}$	104	$^\circ\text{C}/\text{W}$
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}$	-160			V
Collector to emitter breakdown voltage	V_{CE0}	$I_C = -1.0\text{mA}$	-150			V
Emitter to base breakdown voltage	V_{EBO}	$I_E = -10 \mu\text{A}$	-5.0			V
Collector cutoff current	I_{CBO}	$V_{CB} = -120\text{V}, I_E = 0$			-50	nA
		$V_{CB} = -120\text{V}, T_A = 100^\circ\text{C}$			-50	μA
DC current gain	h_{FE}	$I_C = -1.0\text{mA}; V_{CE} = -5.0\text{V}$	50			
		$I_C = -10\text{mA}; V_{CE} = -5.0\text{V}$	60		240	
		$I_C = -50\text{mA}; V_{CE} = -5.0\text{V}$	50			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}; I_B = -1.0\text{mA}$			-0.2	V
		$I_C = -50\text{mA}; I_B = -5.0\text{mA}$			-0.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}; I_B = -1.0\text{mA}$			-1.0	V
		$I_C = -50\text{mA}; I_B = -5.0\text{mA}$			-1.0	V
Output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$			6.0	pF
Transition frequency	f_T	$I_C = -10\text{mA}; V_{CE} = -10\text{V}; f = 100\text{MHz}$	100		300	MHz